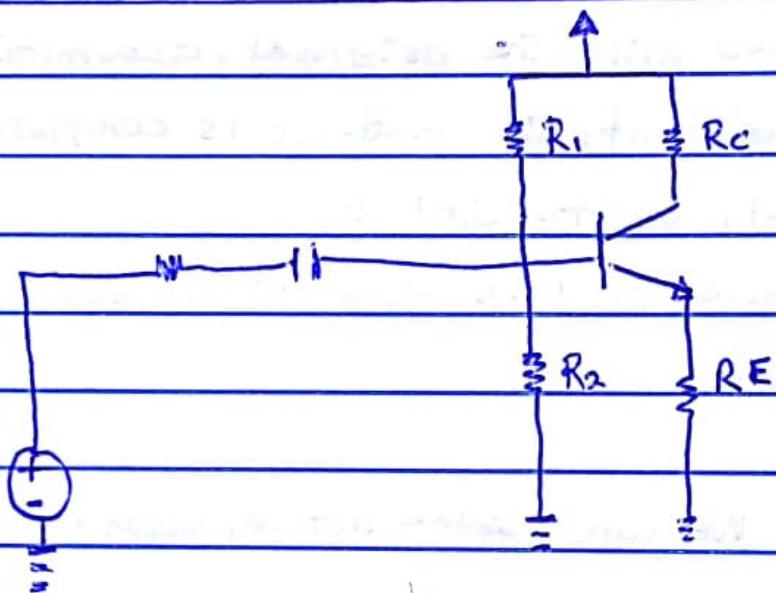


22/11/22 DC Analysis of Voltage Dividers Bias



DC Analysis of BJT Amplifier Circuits

DC analysis of a common Emitter Amplifier circuits begins with determining the DC bias values and then removing coupling and by pass capacitors, the load resistor and signal sources to produce the equivalent circuit by applying the Thevenin's Theorem and KVL

Steps for DC Analysis of BJT circuits

\Rightarrow To analysis BJT circuits with DC source must follow

These five steps

- 1 Assume an Operating Mode.
- 2 Enforce the equality condition of that mode.
- 3 Analyze the circuit with the Enforce condition
- 4 Check the inequality condition of the mode for consistency with the original assumption
IF consistent, the analysis is complete, if inconsistent, Go to step 5.
- 5 Modify your original assumption and Repeat the steps.

(i) Assume: We can assume active, saturation or cutoff mode

(ii) Enforce:

Active mode \rightarrow (f.B)

(a) $V_{BE} = 0.7V$ (nPN), $V_{EB} = 0.7V$ (PnP)

(b) $I_C \propto I_B$

$I_C = \beta I_B$ β (current gain Amplifying function)

$I_C = \alpha I_E$

$I_E = (\beta + 1) I_B$

Saturation Mode →

(a) $V_{BE} = 0.7V(npn) \mid 0.3V$

$$V_{EB} = 0.7V(PNP) \mid 0.3V$$

(b) $V_{CB} = -0.5V(npn)$

$$V_{CB} = -0.5V(PNP)$$

(c) $-V_{CE} = -2V(npn)$

$$-V_{EC} = 0.2V(PNP)$$

Cutoff Mode →

No current flow we can enforce

$$I_C = 0 \quad I_E = 0 \quad I_B = 0$$

(m) Analyze:

- Active: The task in dc analysis of a BJT in active mode is to find one unknown current and one additional unknown voltage

(a) $I_C = \beta I_B$

$$I_E = I_C + I_B$$

$$I_E = (\beta + 1) I_B$$

(b) $V_{BE} = 0.7V$

$$V_{CE} = V_{CB} + V_{BE} \text{ (nPNP)}$$

$$V_{EC} = V_{BC} + V_{EB} \text{ (PnPNP)}$$

For active Analysis: $I_B, I_C, I_E, V_{CE}, V_{CB}$

- Saturation: We know all BJT voltage but know nothing about BJT current.

I_B, I_C, I_E

- Cutoff Mode: All the currents are zero
 V_{BE}, V_{CB}, V_{CE} (any 2)

(4)

CHECK:

- Active $V_{CB} > 0$

$V_{CE} \geq 0.7$

$I_B > 0$

$I_C > 0, I_E > 0$

- Saturation

$I_C < \beta I_B$

$I_B > 0, I_C > 0, I_E > 0$

- Cutoff: V_{BE}, V_C

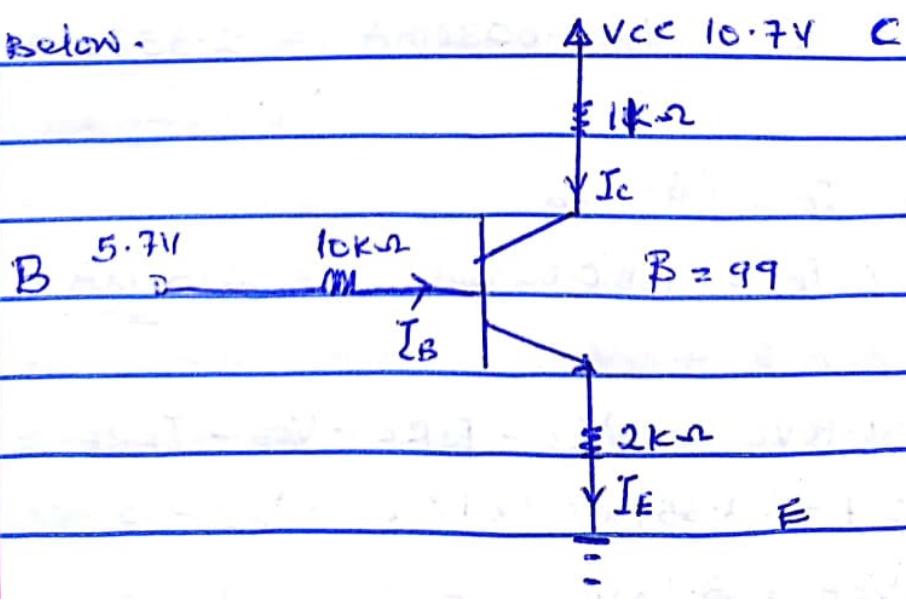
If the result of our analysis are consistent with each of these metricality, then we have made the correct analysis.

However, if any of the assumption is not correct, then we have made the wrong assumption.

- (5) MODIFY :- If one or more of the BJT are not in active mode, then it must be either cutoff or saturation. We must change our assumption and start all over again.

Example 2.

Determine I_B , I_c , I_E , V_{ce} , V_{cb} and V_B in the circuit below.



Assuming Active mode :-

$$V_{BE} = 0.7V$$

$$\Rightarrow \text{Input KVL} = V_B - I_B R_B - V_{BE} - I_E R_E = 0$$

$$5.7 - I_B (10 \times 10^3) - 0.7 - I_E (2 \times 10^3) = 0$$

$$5 - I_B (10 \times 10^3) - I_E (2 \times 10^3) = 0$$

$$\text{But } I_E = (\beta + 1) I_B$$

$$I_E = (99 + 1) I_B = 100 I_B$$

$$5 - I_B (10 \times 10^3) - 100 I_B (2 \times 10^3) = 0$$

$$5 - 1000 I_B - 200000 I_B = 0$$

$$I_B = \frac{5}{210000} = 0.0238 \text{ mA}$$

$$\text{From : } I_C = \beta I_B$$

$$I_C = 99 \times 0.0238 \text{ mA} = 2.357 \text{ mA}$$

$$\text{from } I_E = (\beta + 1) I_B$$

$$I_E = (100) 0.0238 \text{ mA} = 2.38 \text{ mA}$$

$$\Rightarrow \text{Output KVL} = V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

$$10.7 - (2.357 \times 10^{-3} \times 1 \times 10^3) - V_{CE} - (2.35 \times 10^{-3} \times 2000) = 0$$

$$V_{CE} = 3.58 \text{ V}$$

$$\Rightarrow V_C = V_{CC} - I_C R_C$$
$$= 10.7 - (2.357 \times 10^{-3} \times 1 \times 10^3)$$
$$= 8.34V$$

$$\Rightarrow V_E = I_E R_E$$
$$= (2.357 \times 10^{-3} \times 2 \times 10^3)$$
$$= 4.76V$$

$$\Rightarrow V_{CE} = V_C - V_E$$
$$= (8.34 - 4.76)V$$
$$= 3.58V$$

$$\Rightarrow V_{CB} = V_{CE} - V_{BE}$$
$$= (3.58 - 0.7)V$$
$$= 2.88V$$

$$I_B = 0.0238mA \quad V_E = 4.76V$$

$$I_C = 2.357mA \quad V_{CE} = 3.58V$$

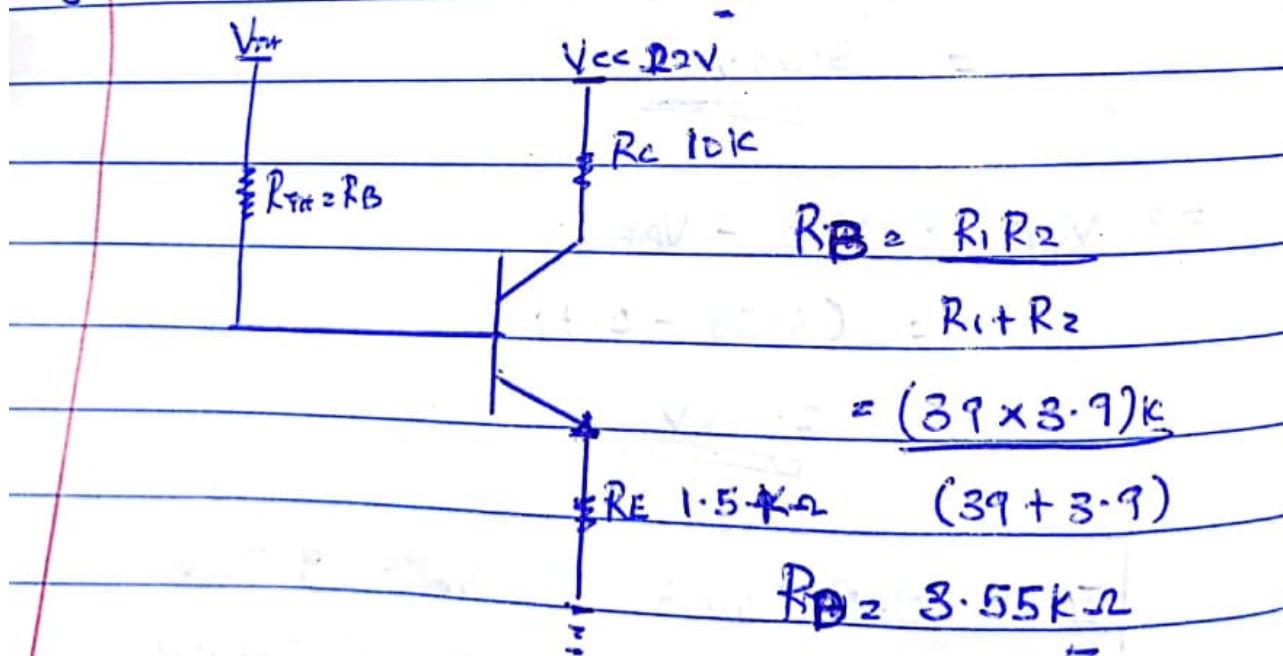
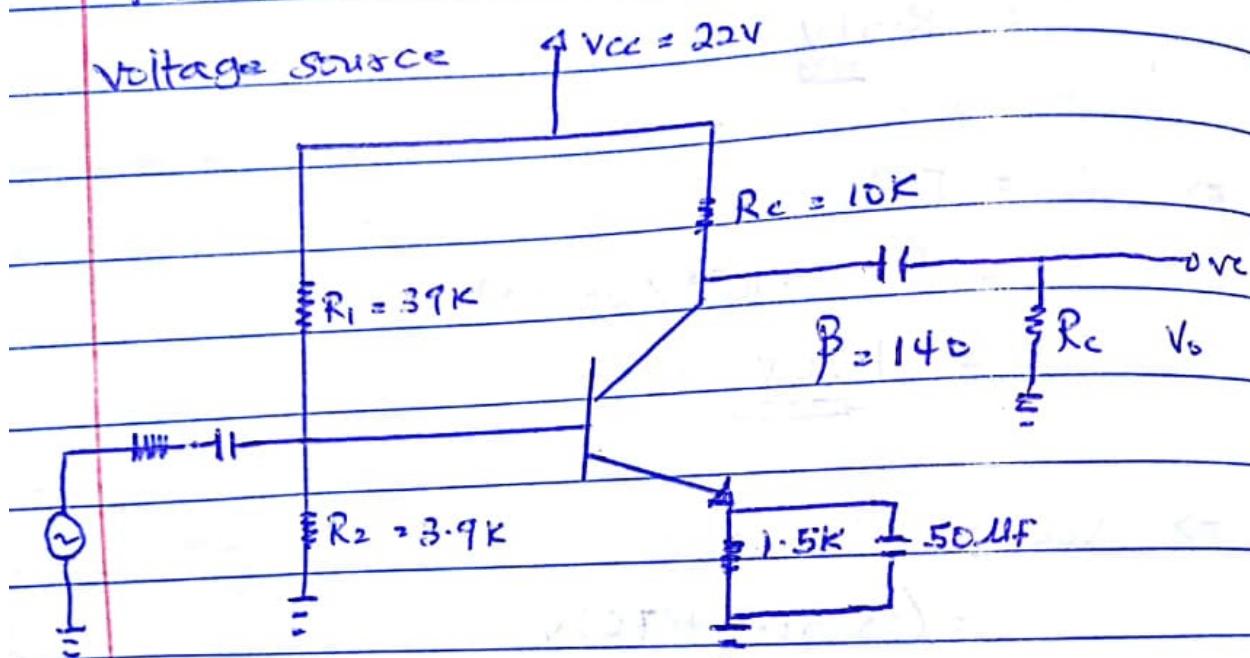
$$I_E = 2.38mA \quad V_{CB} = 2.88V$$

$$V_{CE} = 3.58V$$

$$V_C = 8.34V$$

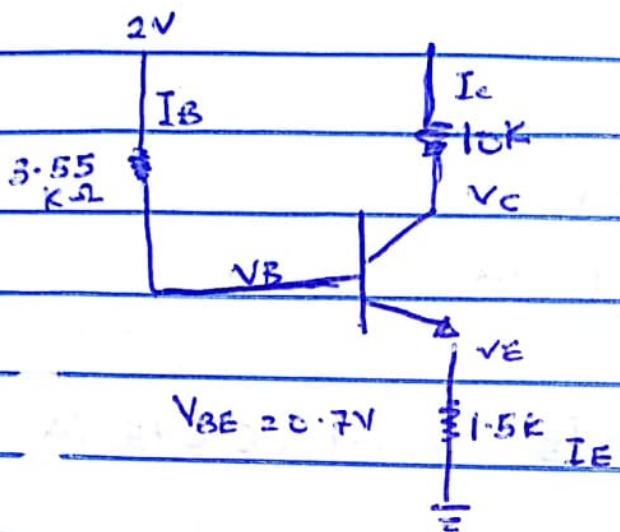
Approximate Analysis.

From diagram one. Remove the capacitor, the voltage source



$$V_{in} = \frac{R_2}{R_1 + R_2} \times V_{cc} \quad (\text{Using Voltage Divider Rule})$$

$$= \frac{3.9K}{(3.9 + 3.9K)} \times 22V = 2V$$



$$\Rightarrow \text{Output KVL} \Rightarrow V_{cc} - I_c R_c - V_{ce} - I_e R_E = 0$$

$$\text{But } I_c = \beta I_B, \quad I_E = I_c + I_B = (\beta + 1) I_B$$

$$I_c = 140 I_B$$

$$I_E = 141 I_B$$

$$22 - (140 I_B)(10k) - V_{ce} - (141 I_B)(1.5k) = 0$$

$$22 - 10k I_c - V_{ce} - 1.5k I_E = 0 \dots \textcircled{4}$$

$$\Rightarrow \text{Input KVL} \Rightarrow V_{in} - I_B R_B - V_{be} - I_E R_E = 0$$

$$2 - 3.55k I_B - 0.7 - 1.5k I_E = 0 \dots \textcircled{ii}$$

$$\Rightarrow \text{If } \beta R_E > I_B R_2$$

$$I_c \approx I_E$$

$$\text{Substitute } I_E = 141 I_B \text{ into eqn } \textcircled{ii}$$

$$2 - 3.55k I_B - 0.7 - 1.5k(141 I_B) = 0$$

$$2 - 3550 I_B - 0.7 - 21150 I_B = 0$$

$$I_B = \underline{1.3}$$

$$\underline{215050}$$

$$I_B = \underline{6.045\text{mA}}$$

$$I_E = 141 I_B = 141 \times 6.045\text{mA} = \underline{\underline{0.852\text{mA}}}$$

$$I_C = 140 I_B = 140 \times 6.045\text{mA} = \underline{\underline{0.846\text{mA}}}$$

From Equation One²:

$$V_{CE} = 22 \mp 10k(0.846\text{mA}) \mp 1.5k(0.852\text{mA})$$

$$V_{CE} = \underline{12.25\text{V}}$$

Half-Biased?

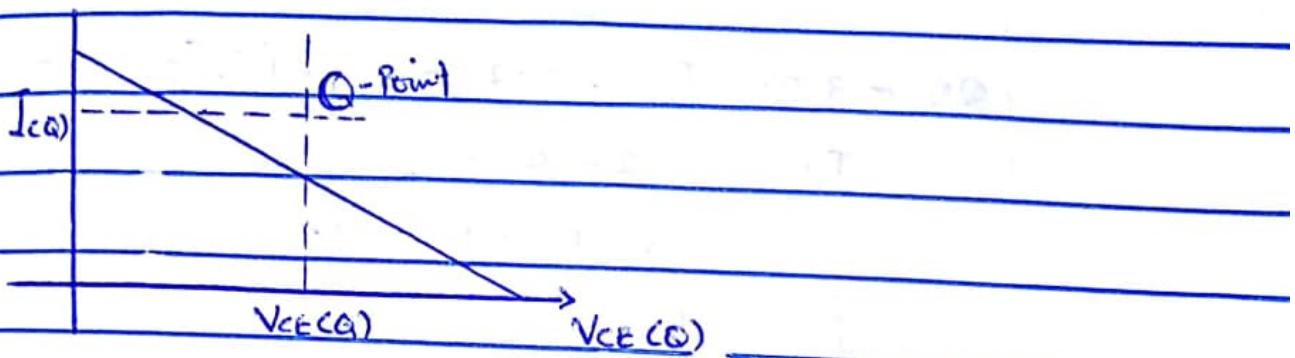
$$V_{CE} = \frac{1}{2} V_{CC}$$

$$= \frac{1}{2} \times 22 = \underline{\underline{11\text{V}}}$$

C_Q-Point (V_{CEQ} , I_{CQ})

$$= (12.25\text{V}, 0.846\text{mA})$$

Diagram



β change $\beta = 70$ is amplification factor for common emitter.

α is amplification factor for common base

γ is amplification factor for common collector.

$$\text{Input KVL} = V_{RH} - I_B R_B - V_{BE} - I_E R_E = 0$$

$$2 - 3.55K I_B - 0.7V - 1.5K I_E = 0 \dots \textcircled{1}$$

$$I_C = \beta I_B$$

$$I_C = 70 I_B$$

$$I_E = I_C + I_B$$

$$I_E = 71 I_B$$

$$I_E = (\beta + 1) I_B$$

$$\text{Output KVL: } V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

$$22 - 10K I_C - V_{CE} - 1.5K I_E = 0 \dots \textcircled{2}$$

Approximate Analysis

$$\beta R_E \geq 10 R_2$$

$$70(1.5K) \geq 10(3.9K)$$

$$105K > 39K \therefore I_C \approx I_E$$

$$QV - 3.55kI_B - 0.7 - 1.5k(71I_B) = 0$$

$$I_B = \frac{2 - 0.7}{(3.55 + 106.5)k}$$

$$I_B = \frac{11.81\text{mA}}{71}$$

$$I_E = 71 \times 11.81\text{mA}$$

$$= 0.839\text{mA}$$

$$I_C = 70 \times 11.81\text{mA}$$

$$= 0.8267\text{mA}$$

$$V_{CE} = 22 - 10k(0.8267\text{mA}) - 1.5k(0.839\text{mA})$$

$$V_{CE} = 12.47\text{V}$$

Q-Point (V_{CEQ} , I_{CQ}) (12.47V, 0.827mA)

Assignment 2:

Calculate the DC Bias Voltage V_{CEQ} and I_{CQ}

The network shown below

$$V_{CC} = 12\text{V}, R_C = 1\text{k}\Omega, R_1 = 30\text{k}\Omega, R_2 = 10\text{k}\Omega$$

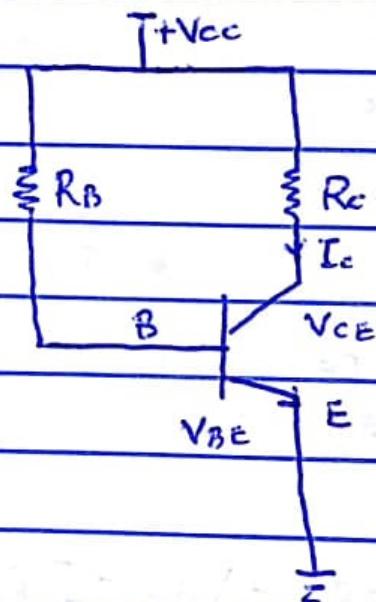
$$R_E = 0.5\text{k}\Omega, C_1 = C_2 = C_{AB} = 10\text{nF}, C_3 = 100\text{nF}$$

$\beta = 99$. Assume Active mode $V_{BE} = 0.7V$

24th November DC Analysis of BJT Amplifiers

Types of DC Biasing

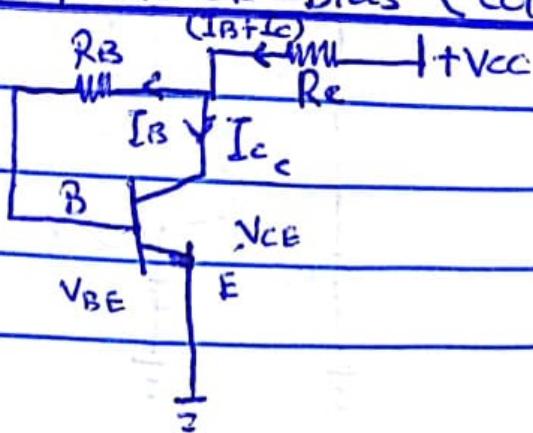
① Fixed Bias (Base Bias)



$$\Rightarrow \text{Input KVL} = +V_{CC} - I_B R_B - V_{BE} - I_C R_C = 0$$

$$\Rightarrow \text{Output KVL} = +V_{CC} - I_C R_C - V_{CE} = 0$$

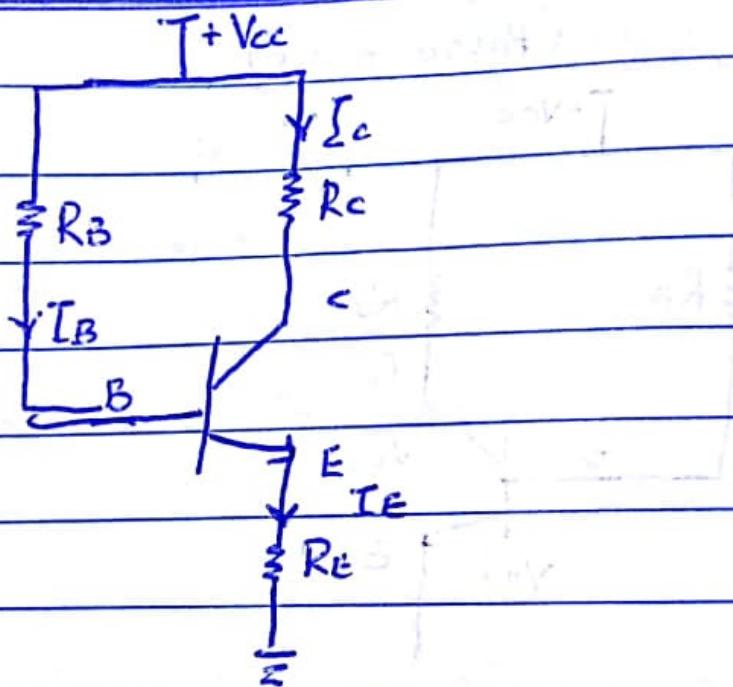
② Collector feedback Bias (Collector Base Bias)



$$\Rightarrow \text{Input KVL} = +V_{CC} - R_C(I_B + I_C) - I_B R_B - V_{BE} = 0$$

$$\Rightarrow \text{Output KVL} = +V_{CC} - R_C(I_B + I_C) - V_{CE} = 0$$

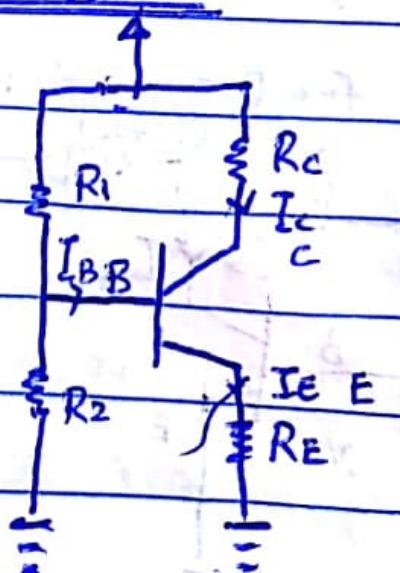
③ Fixed Bias with Emitter Resistor.



$$\Rightarrow \text{Input KVL} = +V_{CC} - I_B R_B - V_{BE} - I_E R_E = 0$$

$$\Rightarrow \text{Output KVL} = +V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

④ Voltage Divider Bias



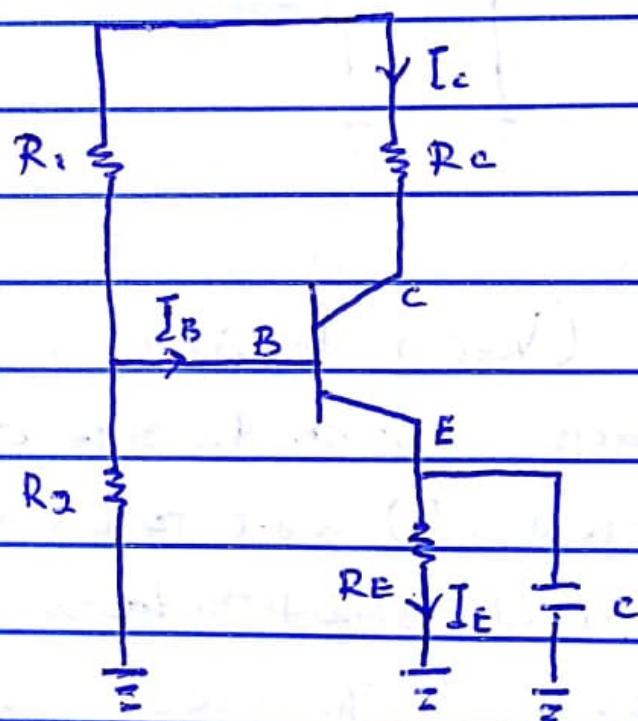
$$\Rightarrow \text{Input KVL} = V_{TH} - I_B R_B - V_{BE} - I_E R_E = 0$$

$$\Rightarrow \text{Output KVL} = V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

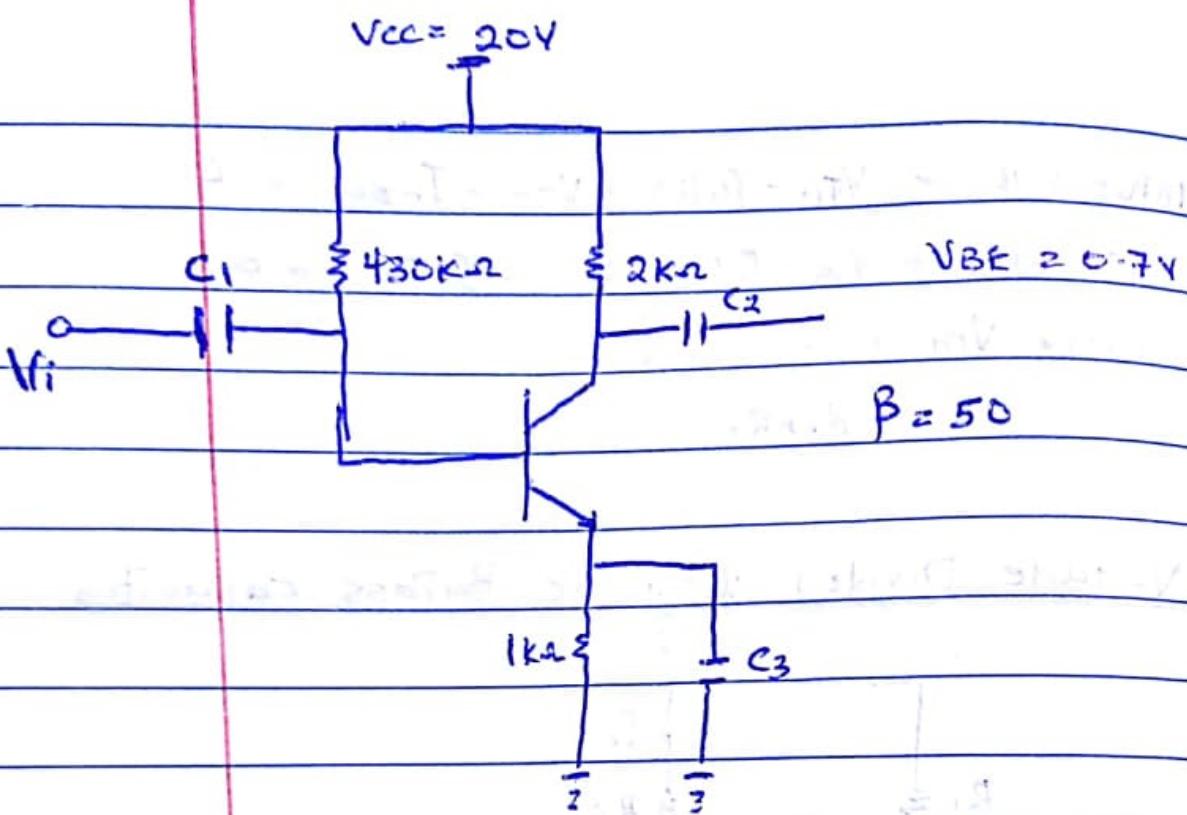
$$\Rightarrow \text{where } V_{TH} = R_2 \times V_{CC}$$

$$R_1 + R_2$$

⑤ Voltage Divider with AC Bypass capacitor:



Example: find the Q-point and the stability factor of the circuit given below



solution

$$Q\text{-point} = (V_{CEQ}, I_{CQ})$$

Stability factor indicate the rate of change in collector current (I_c) w.r.t to change in collector leakage current. Stability factor should be as low as possible. Anything above "25" would result in unsatisfactory performance of the transistor Amplifier.

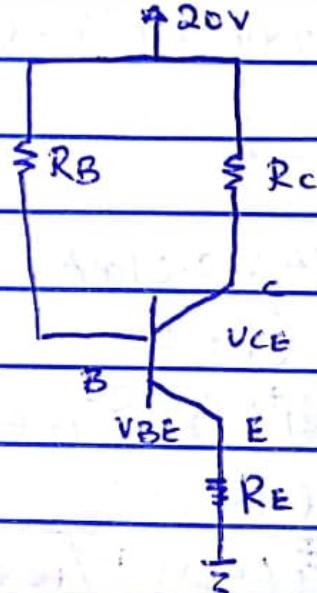
$$\text{Stability factor (s)} = (1 + \beta)$$

$$1 + \beta \left[\frac{R_E}{R_E + R_B} \right]$$

$$s < 25$$

Very important

Step one: We start by opening all capacitors



$$\Rightarrow \text{Input KVL} = V_{cc} - I_B R_B - V_{BE} - I_E R_E = 0$$

$$I_E = (\beta + 1) I_B$$

$$= 20 - R_B I_B - V_{BE} - (\beta + 1) R_E I_B = 0$$

$$I_B = \frac{V_{cc} - V_{BE}}{R_B + (\beta + 1) R_E} = \frac{20 - 0.7}{430K + (51) 1K_2}$$

$$= 40 \mu A$$

$$I_C = \beta I_B = 51 \times 40 \mu A = 2.04 mA$$

$$I_E = (\beta + 1) I_B = 51 \times 40 \mu A = 2.04 mA$$

$$\Rightarrow \text{Output KVL} = V_{cc} - I_E R_C - V_{ce} - I_E R_E = 0$$

$$V_{CE} = 20 - (2.04 \times 10^{-3} \times 10^3) - (40 \times 10^{-6} \times 430 \times 10^3)$$

$$V_{CE} = 20 - (2.04 \times 10^3 \times 10^3) - (2 \times 10^3 \times 2.01 \times 10^{-3})$$

$$V_{CE} = 13.94V$$

Q-Point = (13.94V, 2.01mA)

$$\text{Stability factor} = \frac{(1 + \beta)}{\frac{1 + (\beta)}{1 + (50)} \left[\frac{R_E}{R_E + R_B} \right]}$$

$$= \frac{50}{50} = 45.69$$

The circuit is less stable

⇒ Coupling capacitor

C_1 and C_2 are coupling capacitors, they're used in the ~~amplifier~~^{amplifiers} circuit to isolate DC, so that the biasing of the amplifier is not disturbed. Therefore:

- ① It allows AC and DC voltage to be applied to the transistors without affecting each other.

- (2) Increase coupling between the input and output AC signals.
- (3) coupling the base and collector current of the transistor.
- (4) increase the DC voltage gain.

\Rightarrow By-Pass Capacitor

It allows AC signals to bypass the emitter resistor. This effectively removes it from the output gain equation resulting in an increase in the amplifier AC gain.

Relationship between α , β and γ

- (1) Amplification factor in common Base configuration " α "

There are two types of α

$$\begin{cases} \alpha_{dc} \\ \alpha_{ac} \end{cases}$$

$$\alpha_{dc} = I_c / I_E$$

$$\alpha_{ac} = \Delta I_c / \Delta I_E \quad | V_{CB} = \text{constant}$$

- (2) Amplification factor for common Emitter configuration " β "

$$\beta_{dc} = I_c / I_B$$

$$\beta_{ac} = \Delta I_c / \Delta I_B \quad | V_{CB} = \text{constant}$$

(3) Amplification factor in common collector configuration

$$\gamma_{DC} = \frac{I_E}{I_B}$$

$$\gamma_{AC} = \frac{\Delta I_E / \Delta I_B}{V_{CE} = \text{constant}}$$

$$I_E = I_c + I_B$$

$$\frac{I_E}{I_B} = \frac{I_c}{I_B} + \frac{I_B}{I_B}$$

$$\boxed{\gamma = \beta + 1} \quad \text{Relationship between } \gamma \text{ and } \beta$$

From :- $\beta = \frac{\alpha}{1 - \alpha}$

$$\gamma = \frac{\alpha}{1 - \alpha} + 1$$

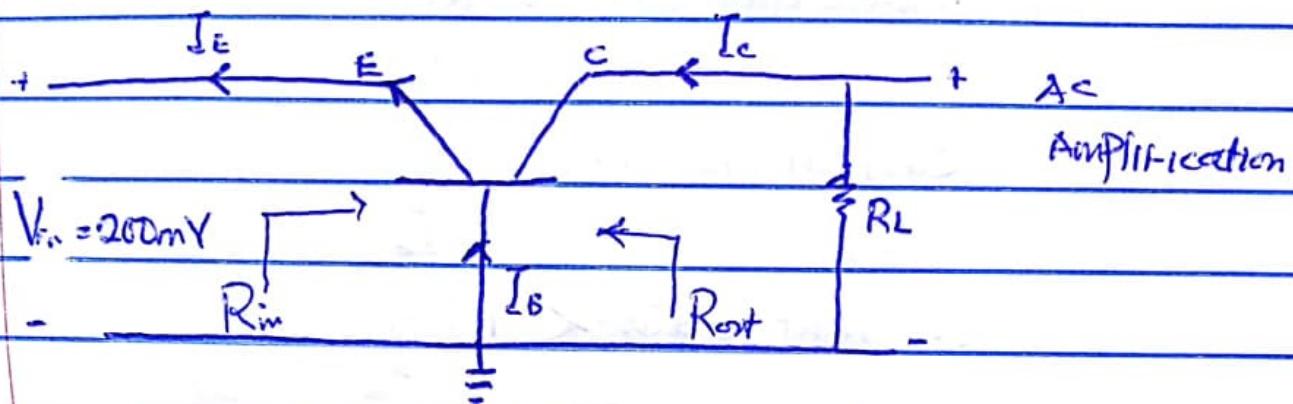
$$\boxed{\gamma = \frac{1}{1 - \alpha}}$$

Relationship between γ and α

$$\gamma = \beta + 1 = \frac{1}{1 - \alpha}$$

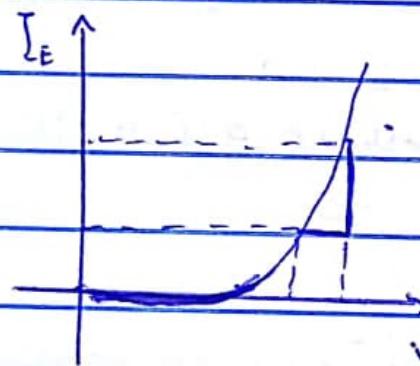
Relationship between α, β and γ

Example • Transistor Amplification Action



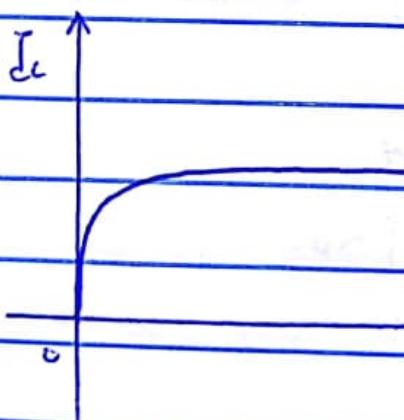
$$V_i = 200\text{mV}$$

$$I_E = \frac{V_i}{R_i}$$



$$V_i = I_i \cdot R_i = I_E R_i$$

$$\frac{\text{slope}}{R_i} = \frac{\Delta I_E}{\Delta V_i}$$



$$\text{slope} = 0 \text{ (slope of a straight line)}$$

$$\alpha \ll 1 \quad [\text{within the range } 0.95 - 0.99]$$

$$I_C = \alpha I_E \text{ since } \alpha \approx 1$$

$$I_C = I_E$$

$$V_{out} = I_c R_{out}$$

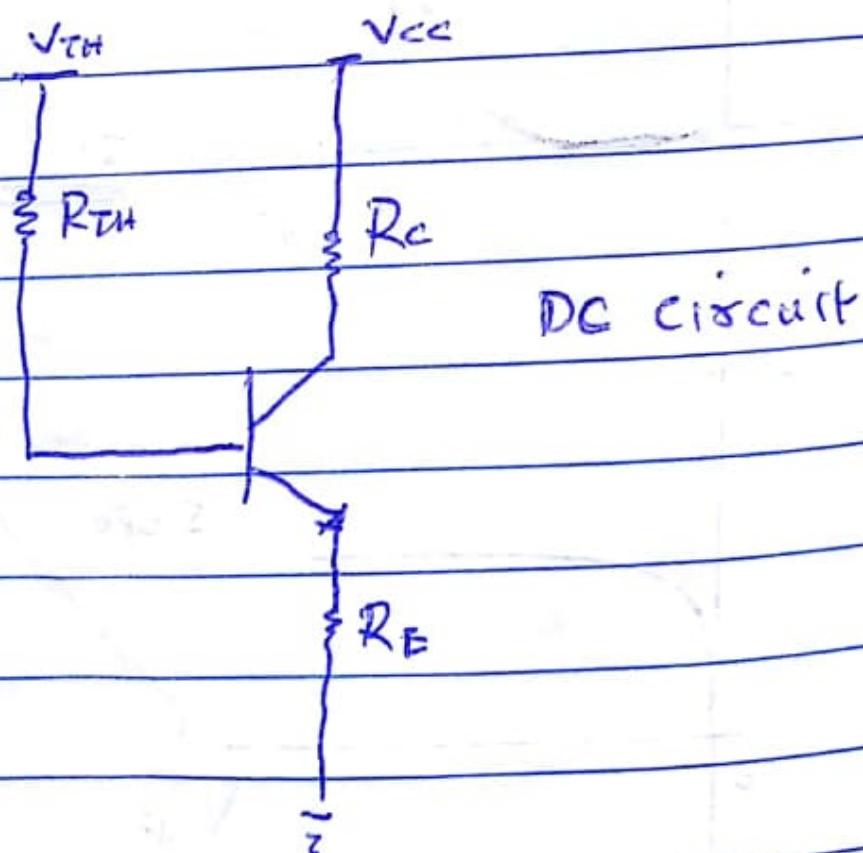
$$\text{Voltage Gain (A}_v\text{)} = \frac{V_{out}}{V_{in}}$$

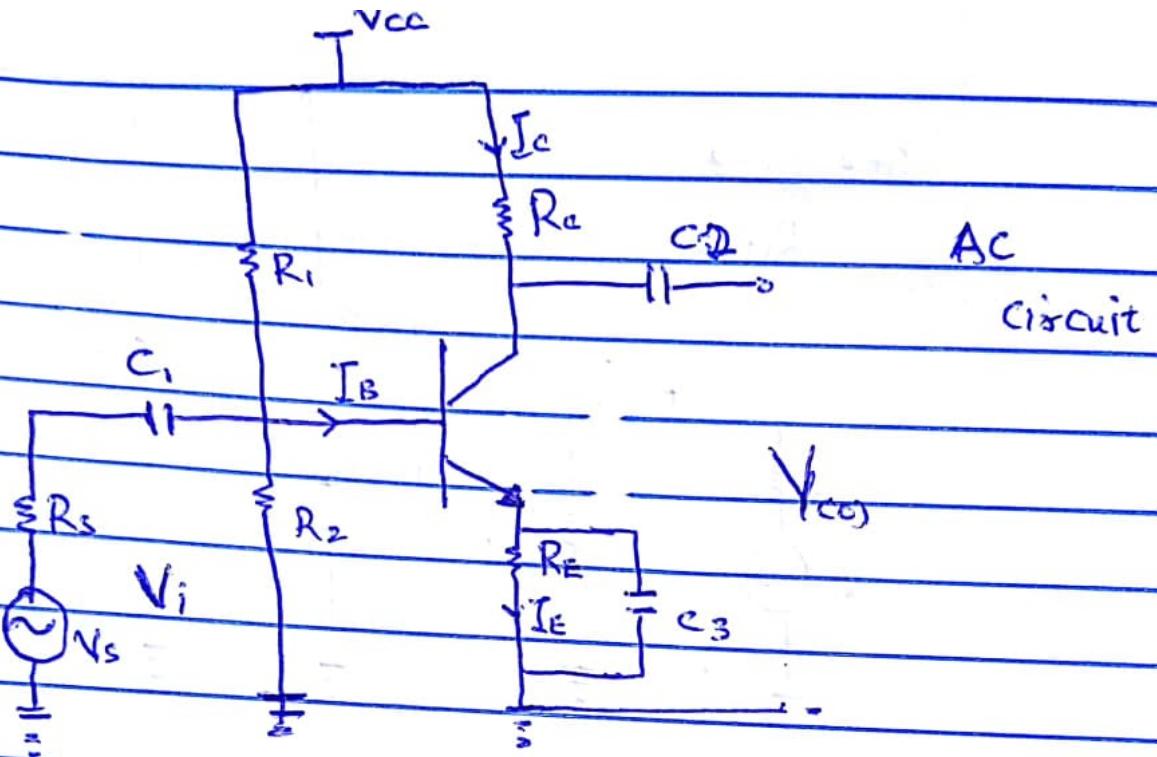
$$\text{Current Gain (A}_i\text{)} = \frac{I_c}{I_E}$$

(Current Gain < 1) Always

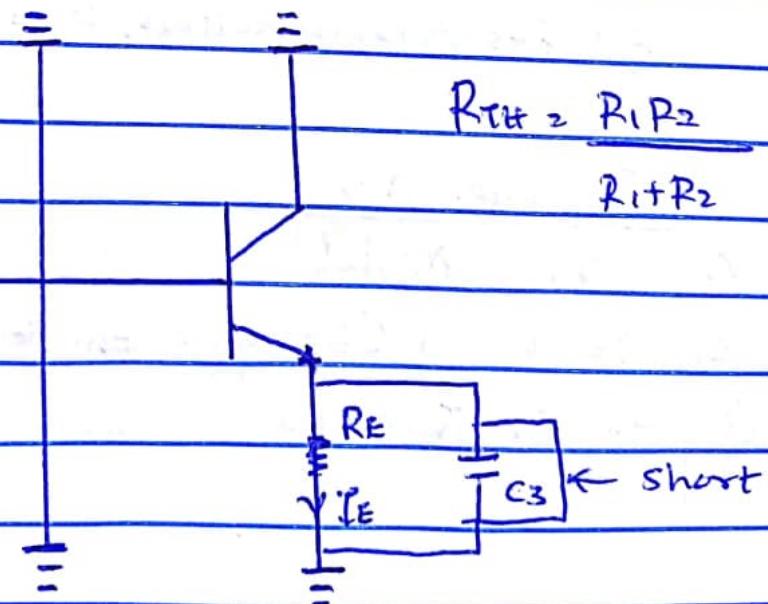
Ac Equivalent Circuit (AC Analysis) of BJT Amplifiers

Ac Equivalent circuit of BJT Amplifier



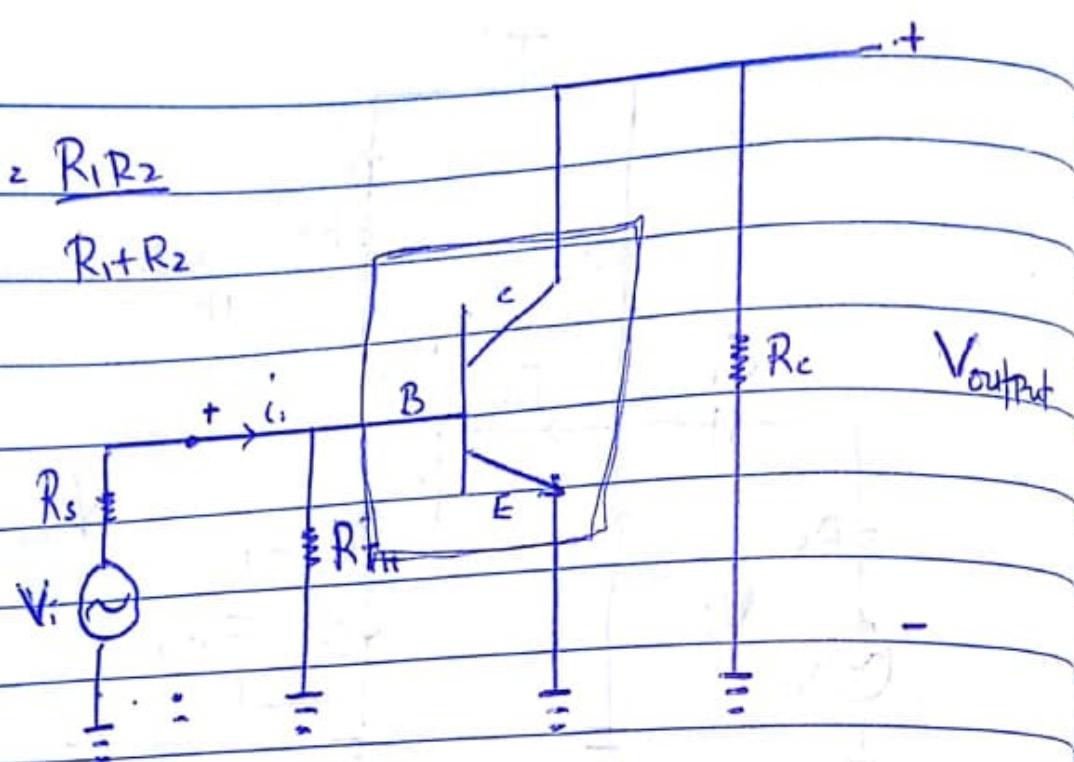


- (1) Step one: Short-circuit all DC sources (connect to ground)
- (2) Step two: Short all capacitors
- (3) Step three: Redraw the network



$$R_{TH} = R_1 R_2$$

$$R_1 + R_2$$



→ Equivalent model of the Transistor.

Equivalent model is a combination of circuit elements properly chosen to best represent the actual behavior of the device under specified operating conditions.

E.g.: Resistors, capacitors, voltage or current sources

Transistor Model

- ① Hybrid Model
- ② γ_e model (Dynamic Emitter Resistance Model)
- ③ Hybrid π model

Transistor Models

Hybrid model

π -model
(Dynamic emitter
Resistance model)

Hybrid π
model

are for small signals

Hybrid model: (h -model or h -parameters model)

Hybrid model is the equivalent model of transistors used in small signal analysis. Hybrid model was widely used in the early years before the popularity of π -model.

In hybrid model, the parameters are defined in general terms for any operating condition, but in case of π -model, the parameters are defined by the actual operating conditions (advantage of π -model).

In hybrid Model, the h -parameters need to be determined, then used to draw the equivalent circuit.

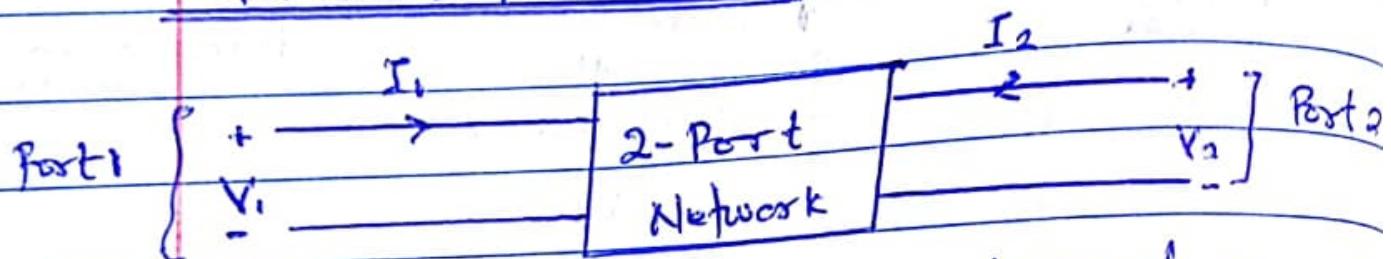
calculation of h -parameters: (h - stands for hybrid)

What is the significance of the word hybrid? Hybrid means "mixed" - These Parameters have mixed dimensions.

These are 4 important parameters in the small-signal

amplifiers and they can be obtained using only Impedance (Z-Parameters) or Admittance (Y-Parameters).

General 2-Port Network:



We are only interested in the terminal currents and terminal voltages. Transistor circuit is also a 2-Port Network.

Total current/voltage = dc Value + ac Values

I_1 , I_2 , V_1 , V_2 are sum of their respective dc and ac values.

Taking 2 quantities as dependent variables and the other 2 quantities as independent variables.

Let say: V_1 & I_2 \Rightarrow Dependent Quantities

V_2 & I_1 \Rightarrow Independent Quantities

Let say: $V_1 = f_1(I_1, V_2)$

$I_2 = f_2(I_1, V_2)$

we can find the changes in V_1 and I_2 as

Total differentials :-

$$dV_1 = \frac{\partial V_1}{\partial I_1} \cdot dI_1 + \frac{\partial V_1}{\partial V_2} \cdot dV_2 \dots \dots \quad (1)$$

similarly,

$$dI_2 = \frac{\partial I_2}{\partial I_1} \cdot dI_1 + \frac{\partial I_2}{\partial V_2} \cdot dV_2 \dots \dots \quad (2)$$

$\Rightarrow \frac{\partial V_1}{\partial I_1}$ \Rightarrow has a unit of impedance ($1 - \text{e}^{\frac{V}{I}}$) $= h_{11}$

$\frac{\partial V_1}{\partial V_2}$ \Rightarrow Dimensionless $= h_{12}$ (voltage gain)

$\frac{\partial I_2}{\partial I_1}$ \Rightarrow Dimensionless $= h_{21}$ (current gain)

$\frac{\partial I_2}{\partial V_2}$ \Rightarrow has unit of Admittance $= h_{22}$

We can re-write equations (1) and (2) as:

$$\begin{aligned} V_1 &= h_{11} I_1 + h_{12} V_2 \dots \dots (3) \\ I_2 &= h_{21} I_1 + h_{22} V_2 \dots \dots (4) \end{aligned} \quad \left. \begin{array}{l} \text{Applicable to} \\ \text{all the Transistor} \\ \text{configurations} \\ \text{CB, CE, CC} \end{array} \right\}$$

Make $V_2 = 0$ in equation (3) and (4)

From eqn (3) $\Rightarrow h_{11} = \frac{V_1}{I_1} \Big|_{V_2=0}$ \rightarrow Input impedance with the output

$V_2 = 0$ (By short-circuiting the Voltage)

short circuited
 $\approx \infty Z_i^n$

h_{ie} \rightarrow input impedance for all collector configuration

from eqn ④ $\Rightarrow h_{21} = \frac{i_2}{i_1} \quad (\text{Forward current Gain})$
 $i_1 | V_2 = 0$ when output voltage is shortcircuited

Forward current Gain when the output is short circuited

so we can write:

$$h_i = h_{11} = \frac{V_1}{i_1} \quad \text{and} \quad h_f = h_{21} = \frac{i_2}{i_1}$$

from ③: If $i_1 = 0$

$$h_r = h_{12} = \frac{V_1}{V_2} | i_1 = 0$$

Reverse voltage gain with it input open circuited

from ④

$$h_o = h_{22} = \frac{i_2}{V_2} | i_1 = 0$$

Output Admittance with the input open circuited

so the 4 h-parameters are h_i, h_f, h_r and h_o

h_i	V_1 / i_1 when $V_2 = 0$	input impedance
h_f	i_2 / i_1 when $V_2 = 0$	forward current gain
h_r	V_1 / V_2 when $i_1 = 0$	reverse voltage gain
h_o	i_2 / V_2 when $i_1 = 0$	output admittance

Nomenclature of h-parameters;

$h_{L1} L_2$

where:

- ⇒ L_1 denotes the nature of the parameter as (i/p impedance, forward current gain, Reverse voltage gain or o/p admittance)
- ⇒ L_2 denotes the transistor configuration (C_B , C_E or C_C)

Example:

- (i) If we have input impedance of $C_E \Rightarrow h_{ie}$
- (ii) Reverse Voltage gain of $C_B \Rightarrow h_{rb}$
- (iii) Output Admittance of $C_C \Rightarrow h_{oc}$
- (iv) Forward current gain of $C_B \Rightarrow h_{fb}$
- (v) Write h_{fe} , h_{pc} , h_{ob} , h_{re} and h_{rc} in full.

Hybrid Model Equivalent Circuit

Re-writing equations (3) and (4)

$$V_1 = h_{il} i_1 + h_{r1} V_2 \dots \dots \quad (5)$$

$$i_2 = h_{f1} i_1 + h_{o1} V_2 \dots \dots \quad (6)$$

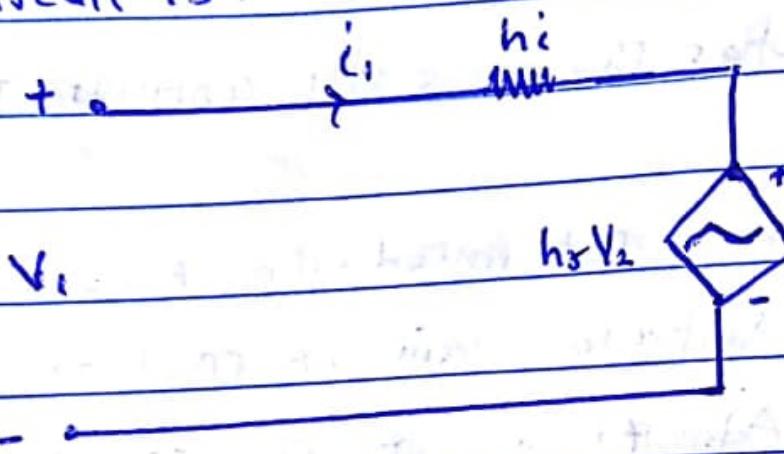
each term of equation (3) is having a unit of Volts:

$$V_1 (\text{Volts}) = h_{il} i_1 (\text{Volts}) + h_{r1} V_2 (\text{Volts})$$

So to obtain the equivalent circuit of equation (5),

$$\text{we will use KVL} \Rightarrow +V_i - h_{i1} i_1 - h_o V_2 = 0$$

The circuit is:

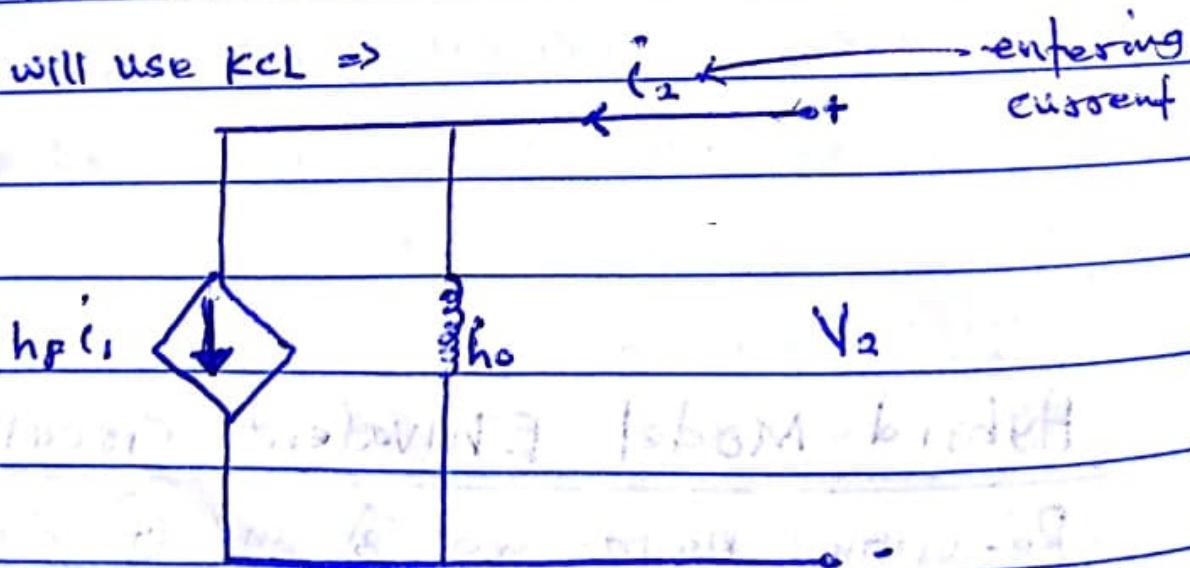


In equation (5), each term is having a unit of Amps.

$$\Rightarrow i_2(A) = h_i i_1(A) + h_o V_2(A)$$

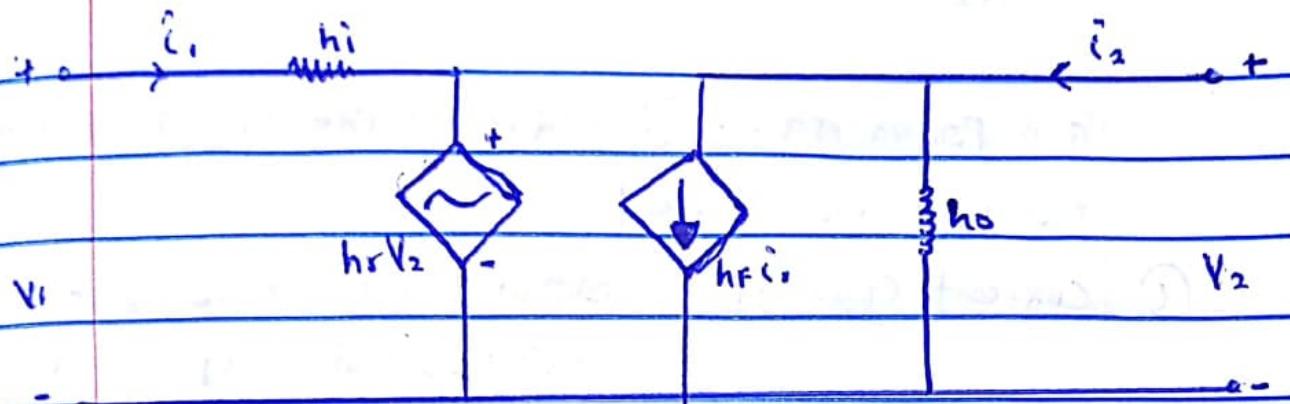
so to obtain the equivalent circuit for equation (6),

we will use KCL \Rightarrow



Therefore by combining the 2 circuits, we will have the final equivalent circuit as:

(efficiency) + (attenuation) = (output) / (input)



for ac analysis, the Transistor is replaced with the small equivalent circuit (General Model). Information like the transistor configuration are not added. Additional subscripts will tell us the transistor configuration.

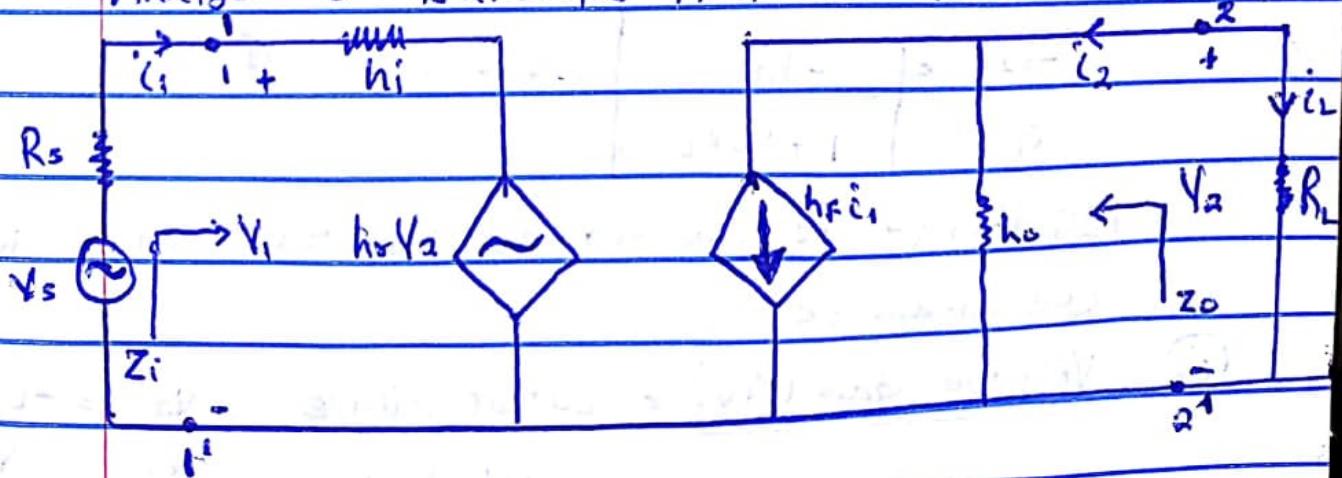
In common-Emitter configuration : $i_1 \rightarrow h_{ie}$

$h_f \rightarrow h_{fe}$

$h_o \rightarrow h_{oe}$, $i_1 = I_B$, $i_2 = I_E$

$h_r = h_{re}$, $V_1 = V_{BE}$, $V_2 = V_{CE}$

Analysis of Transistor Amplifier Using h-Parameters:



To find the expressions for Current gain, Voltage gain

i_L = Load current

and Power gain. [Introducing the i(p) supply and the load Resistance].

(i) Current Gain (A_i) = $\frac{\text{Output current}}{\text{Input current}} = \frac{i_L}{i_1} = -\frac{i_2}{i_1}$

(V_2) = Voltage drop across $R_L = V_2 = i_L R_L = -i_2 R_L$

from eqn (6) or h-parameter equations:

$$i_2 = h_f i_1 + h_o V_2$$

$$i_2 = h_f i_1 + h_o (-i_2 R_L)$$

$$i_2 + h_o i_2 R_L = h_f i_1$$

$$i_2 (1 + h_o R_L) = h_f i_1$$

$$i_2 = \frac{h_f i_1}{1 + h_o R_L}$$

$$(1 + h_o R_L)$$

but the current gain, $A_i = -\frac{i_2}{i_1}$

$$\frac{-i_2}{i_1} = \frac{-h_f}{1 + h_o R_L}$$

(7)

Equation (7) is true for all the transistor configurations (CB, CE and CC)

(ii) Voltage Gain (A_v) = $\frac{\text{Output voltage}}{\text{Input voltage}} = \frac{V_2}{V_1} = -\frac{i_2 R_L}{V_1}$

Input voltage

$$\text{but } A_i = -\frac{i_2}{i_1} \Rightarrow -i_2 = i_1 A_i$$

$$\therefore A_v = \frac{i_1 A_i R_L}{V_i} = \frac{A_i R_L}{Z_i} \quad \dots \quad (8)$$

$$\text{where } Z_i = \frac{V_i}{i_1}$$

$$\text{But } Z_i = \frac{h_{iF} + h_{oR_L}}{h_{oR_L} + h_o} \rightarrow \text{To derive it later}$$

$$\text{But } A_i = \frac{-h_F}{1 + h_o R_L} \quad \text{i.e equation (7)}$$

Now substitute for Z_i and A_i in to equation (8)

$$\Rightarrow A_v = \frac{-h_F R_L}{h_i + (h_i h_o - h_{iF}) R_L}$$

$$\text{where } \Delta h = (h_i h_o - h_{iF})$$

$$\Rightarrow A_v = \frac{-h_F R_L}{h_i + \Delta h R_L} \quad \dots \quad \text{equation (9)}$$

Equation (9) is also true for all the transistor configurations (CE, CB and CC) i.e the expression for voltage gain

(iii)

$$\text{Power Gain, } (A_p) = A_v \times A_i$$

$$A_p = \left[\frac{-h_{FE} R_L}{h_i + \Delta h_{FE} R_L} \right] \times \left[\frac{-h_F}{1 + h_o R_L} \right]$$

2. $A_p = \frac{h_F^2 R_L}{(h_i + \Delta h_{FE} R_L)(1 + h_o R_L)}$... eqn (10)

Equation (10) is the expression for the power gain (A_p) is true for CE, CB and CC configurations

(ii) Overall Voltage Gain (A_{vS}) = V_2/V_S

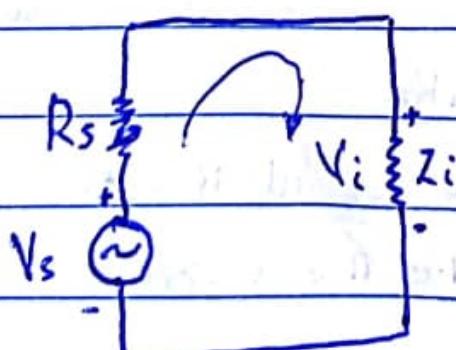
$$A_{vS} = \frac{V_2 \cdot V_i}{V_S \cdot V_i} = \frac{V_2}{V_i} \cdot \frac{V_i}{V_S}$$

but the voltage gain,

$$A_v = V_2/V_i$$

$$A_{vS} = A_v \cdot \frac{V_i}{V_S} \quad \dots \dots \text{eqn (11)}$$

From the circuit, we can redraw the input as:



V_i is the input voltage and
 Z_i is the voltage across Z_i

Using KVL: $V_s - iR_s - iz_i = 0$

$$\Rightarrow i = \frac{V_s}{R_s + Z_i}$$

$$V_i = i_z i$$

$$V_L = Z_i V_s$$

$$R_s + Z_i$$

$$\Rightarrow \frac{V_i}{V_s} = \frac{Z_i V_s}{R_s + Z_i} \times \frac{1}{V_s} = \frac{Z_i}{R_s + Z_i} \dots \text{eqn } 12$$

Substitute eqn 12 into 11

$$A_{VS} = A_V \left(\frac{Z_i}{R_s + Z_i} \right) \dots \text{eqn } 13$$

Equation 13 is the final expression for the overall voltage gain, but if an ideal voltage source is considered

$$V_s = \text{ideal} \rightarrow R_s = 0 \text{ and}$$

$$A_{VS} = A_V \rightarrow \text{for ideal voltage source}$$

(v) Overall Current Gain (A_{IS}): is the ratio of the output current to the current delivered by the source

$$A_{IS} = \frac{i_L}{i_s} \times \frac{i_1}{i_1} = \frac{i_L}{i_s} \times \frac{i_1}{i_1}$$

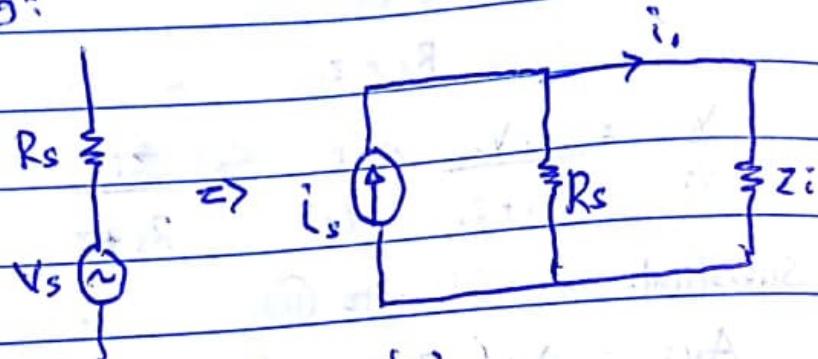
$$\text{and } i_2 = -i_1$$

$$\Rightarrow A_{IS} = \frac{-i_2}{i_s} \cdot \frac{i_1}{i_s} = \boxed{A_i \cdot \frac{i_1}{i_s}} \dots \text{eqn } 14$$

Where $\boxed{A_i = \frac{-i_2}{i_1}}$

To find $i_1/i_s = ?$

converting:



Using current divider rule;

$$i_1 = \left[\frac{R_s}{R_s + Z_i} \right] \times i_s$$

$$\Rightarrow \frac{i_1}{i_s} = \frac{R_s}{R_s + Z_i} \quad \text{eqn (15)}$$

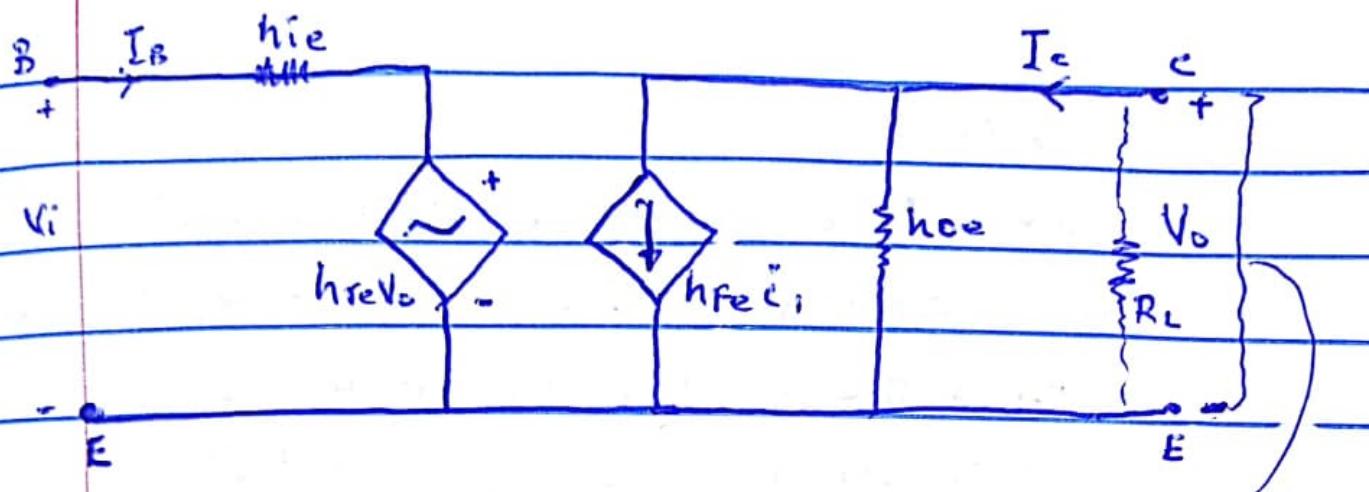
Substitute (15) into (14)

$$A_{is} = A_i \cdot \left[\frac{R_s}{R_s + Z_i} \right] \quad \dots \text{eqn (16)}$$

Equation (16) is the overall expression for the overall current gain. For an ideal current source, the resistance $R_s = \infty$, then:

$$A_{is} = A_i$$

Approximate Hybrid Equivalent Model of C-E Transistor



model for CE configuration

For CE and CB configurations, the magnitude of h_T and h_o are such that the results obtained for the parameters such as Z_i , Z_o , A_v and A_i will not change.

$h_o = \text{output admittance} \Rightarrow 1/h_o = \text{output impedance}$
(Very large)

$$\Rightarrow 1/h_o \gg R_L$$

OR $1/h_o \gg (R_L || R_L)$ - for fixed-bias configuration

$\Rightarrow h_o$ can be replaced with open circuit.

And $h_{re} = V_o \neq 0 \Rightarrow h_{re}V_o \approx 0$, so $h_{re}V_o$ can be replaced with a short circuit

as shown below

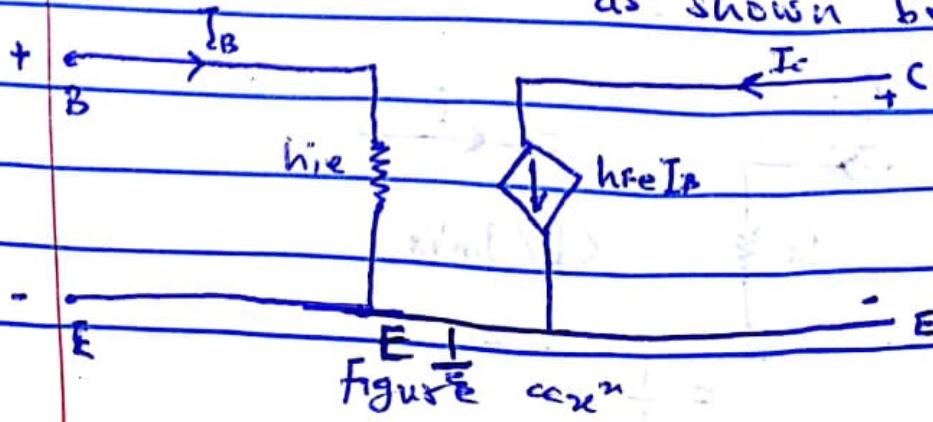


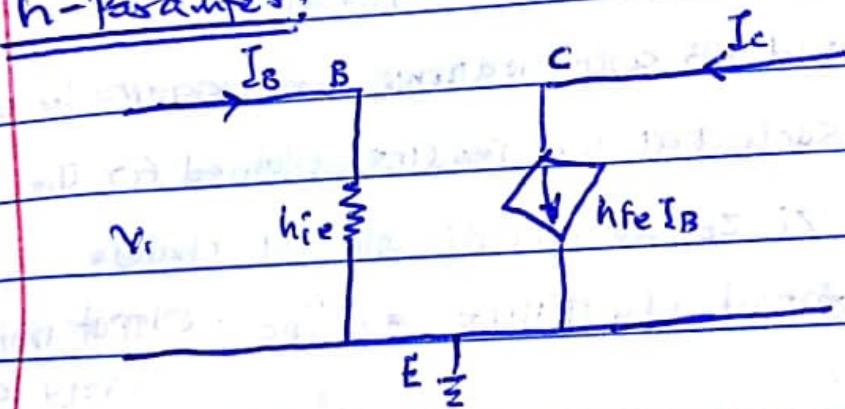
Figure $\frac{1}{2}$ contn

$$i_i = I_B$$

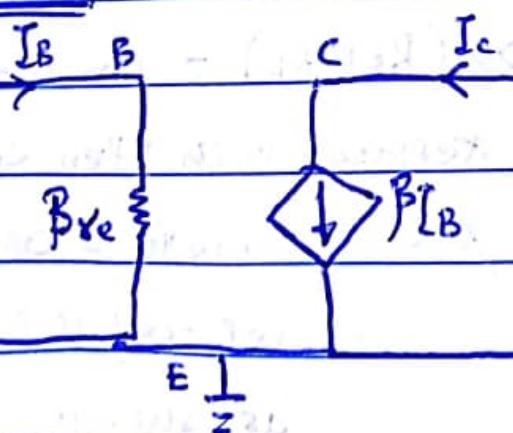
Figure "X" is the approximate equivalent model for the CE configuration and is used to replace the transistor in the small-signal AC analysis.

Comparison of the 3-models of BJT:

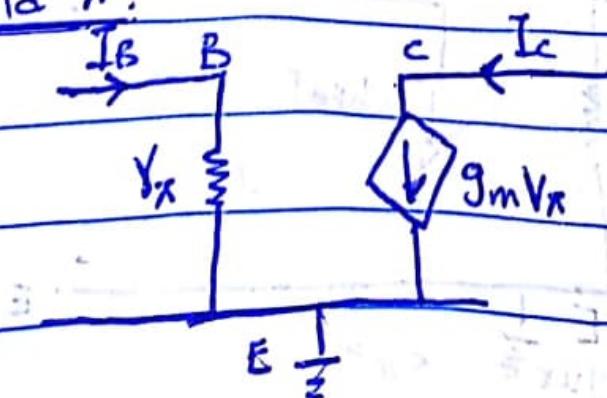
⇒ h-Parameters:



Re-model:



⇒ Hybrid π :



$$\Rightarrow hie \in Pre \equiv \{x \dots\} \quad \textcircled{1}$$

$$\Rightarrow h_{FE} I_B \equiv \beta I_B = g_m V_T \dots \text{Q}$$

Where g_m = Transconductance

What is V_π ? $V_\pi = I_B \gamma_\pi$

$$\Rightarrow h_{FeIB} = \beta I_B = g_m I_B \gamma \pi$$

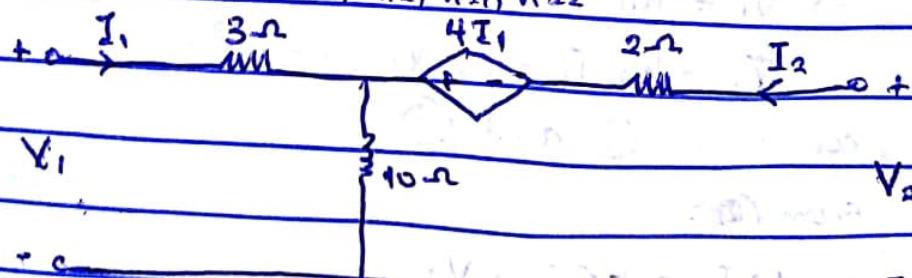
$$\therefore hfe = \beta = g_m/\gamma_n \Rightarrow g_m = \beta/\gamma_n$$

Note:- AC Analysis cannot be carried out without DC Analysis

Transconductance g_m is one expression of the performance of a BJT or FET. In general, the larger the transconductance figure for a device, the greater the gain (Amplification). It is capable of delivering when all other factors are held constant.

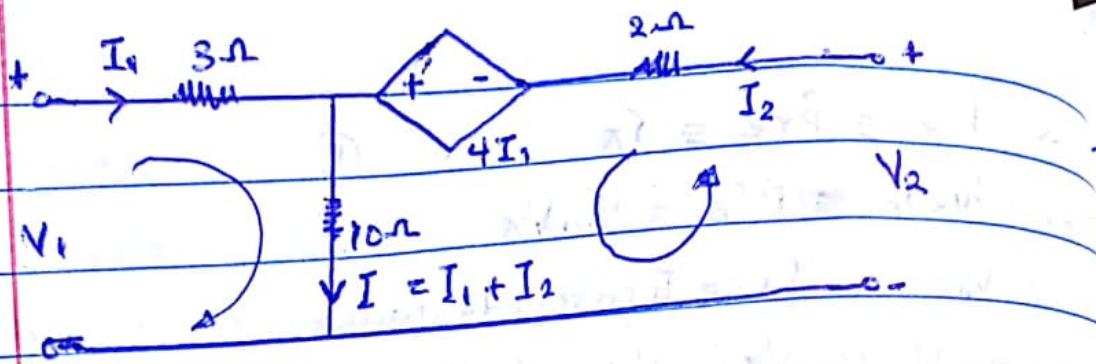
Example: Find the hybrid parameters for the two-port network given below.

Given below. i.e $h_1, h_{12}, h_{21}, h_{22}$



solution

Step one: Mark all the currents in the 2-Port Network



Step 2: Obtain the O/P KVL equation and the Q/P KVI eqn.

Open loop KVI in loop one: $V_1 = 3I_1$

$$+V_1 - 3I_1 - 10(I_1 + I_2) = 0$$

$$V_1 = 13I_1 + 10I_2 \quad \dots \textcircled{1}$$

Open loop KVI in loop two: $V_2 = 2I_2$

$$+V_2 - 2I_2 + 4I_1 - 10(I_1 + I_2) = 0$$

$$V_2 = 6I_1 + 12I_2 \quad \dots \textcircled{2}$$

Remember:

$$\begin{bmatrix} V_1 \\ I_1 \end{bmatrix} \rightarrow \text{Dependent Variables} \quad \begin{bmatrix} I_1 \\ V_2 \end{bmatrix} \rightarrow \text{Independent Variables}$$

$$\Rightarrow V_1 = h_{11}I_1 + h_{12}V_2 \quad \dots \textcircled{3}$$

$$I_2 = h_{21}I_1 + h_{22}V_2 \quad \dots \textcircled{4}$$

Comparing $\textcircled{4}$ and $\textcircled{2}$

From $\textcircled{2}$:

$$12I_2 = -6I_1 + V_2$$

$$I_2 = -\frac{1}{2}I_1 + \frac{1}{12}V_2 \quad \dots \textcircled{5}$$

Substitute earn $\textcircled{5}$ into $\textcircled{1}$:

$$V_1 = 13I_1 + 10I_2$$

$$V_1 = 13I_1 + 10 \begin{bmatrix} -1 & 1 \\ 2 & 12 \end{bmatrix} V_2$$

$$V_1 = 13I_1 - 5I_2 + 5/6 V_2$$

$$V_1 = 8I_1 + 5/6 V_2 \quad \text{--- (4)}$$

Compare eqn (4) and (3):

We can find that

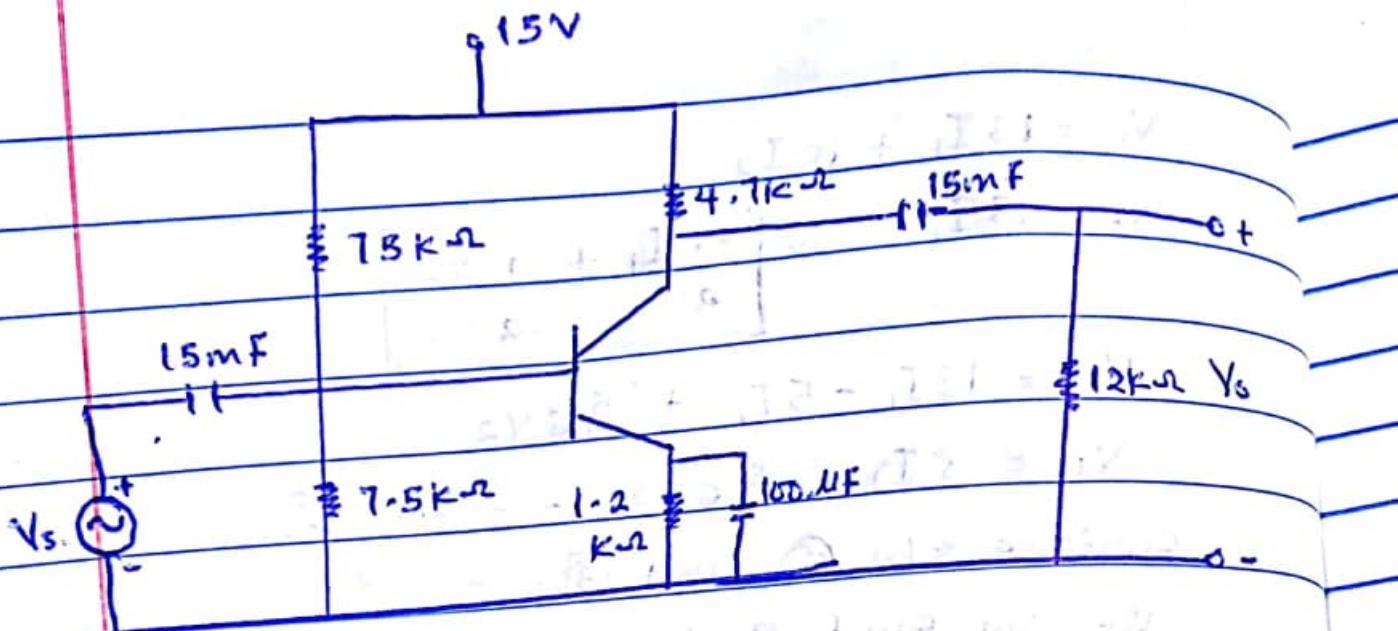
$$h_{11} = 8, h_{12} = 5/6 \quad (\text{no unit})$$

Compare (4) and (5)

$$h_{21} = -1/2, h_{22} = 1/12 \quad (\text{mho or s})$$

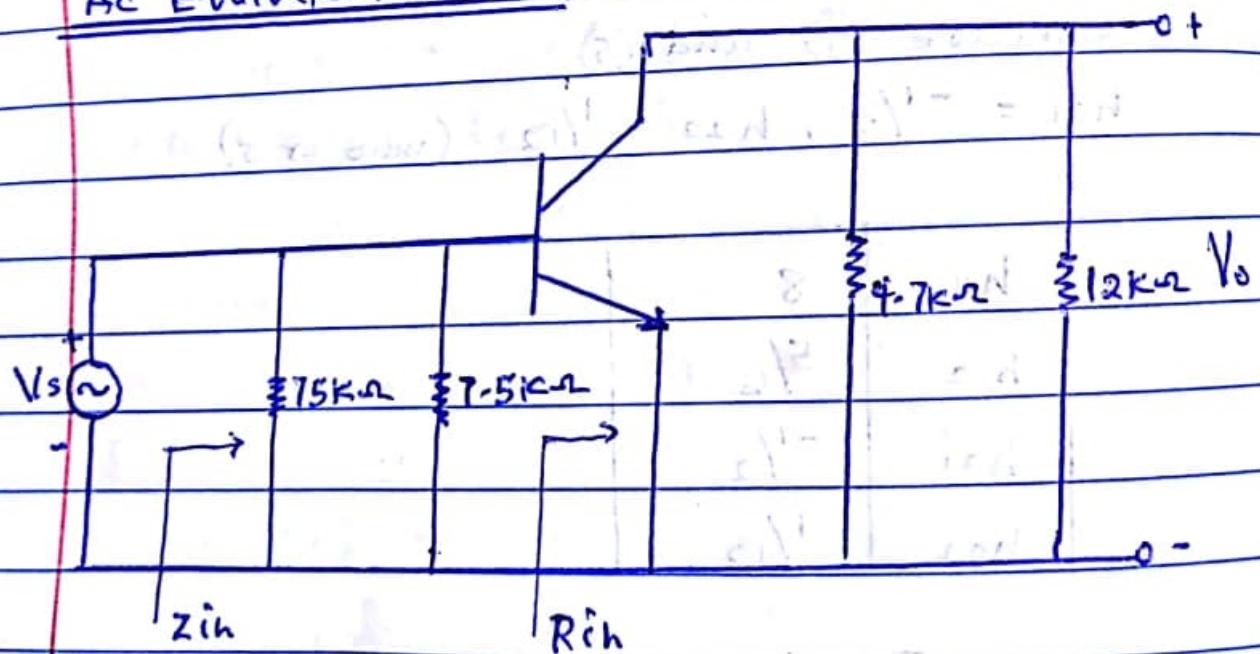
h_{11}	8
h_{12}	$5/6$
h_{21}	$-1/2$
h_{22}	$1/12$

Example:- Determine (i) Voltage gain (ii) Input impedance (iii) Q-point
of the transistor amplifier shown below ($\beta = 100$ and $R_{in} = 2k\Omega$). Neglect V_{BE}



solution:

AC Equivalent Model



①

$$\text{Voltage gain: } A_v = \frac{V_o}{V_i} = -h_{fe} \times R_L$$

$$\Rightarrow R_L = R_{ac} = R_C \parallel R_L = \frac{4.7k \times 12k}{4.7k + 12k} = 3.38k\Omega$$

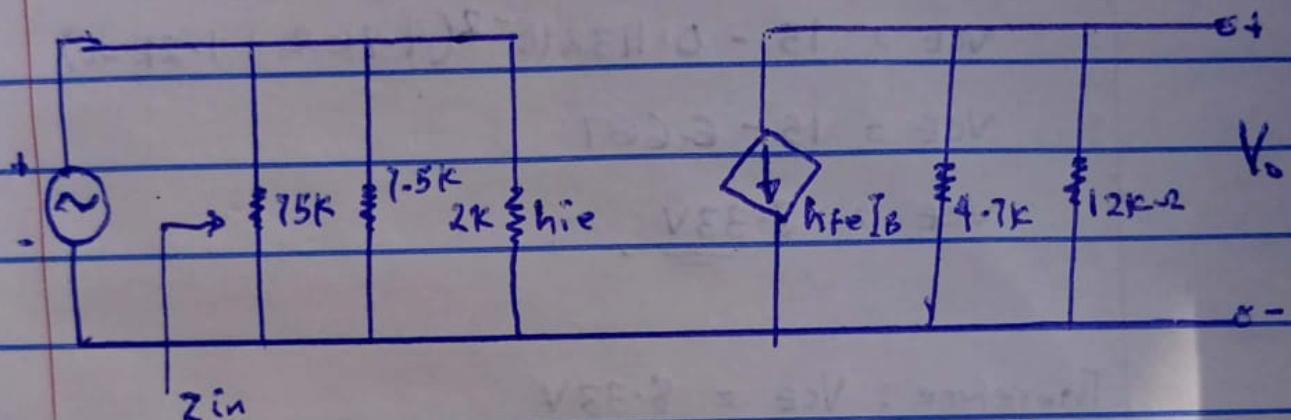
$$h_{FE} = \beta$$

$$\text{And } h_{IE} = Y_{in} = 2K\Omega$$

$$\therefore A_v = -\frac{\beta R_{ac}}{Y_{in}} = -100 \times 3.38k \approx 169$$

$$\therefore A_v = 169$$

(ii) $Z_{in} =$



$$Z_{in} = 75k \parallel 7.5k \parallel 2k$$

$$= 75k \parallel 7.5(2) = 75k \parallel 1.58k$$

$$7.5 + 2$$

(iii) Q-point: DC Analysis (I_{CA} , V_{CEQ})

$$V_B = \frac{R_2}{1+R_2} \cdot V_{CC} = \frac{7.5k}{75k+7.5k} \times 15 = 1.36V$$

$$V_{BE} = V_B - V_E$$

$$V_E = V_{BE} + V_B = 0 + 1.36V \approx 1.36V$$

$$\therefore I_E = \frac{V_E}{R_E} = \frac{1.36}{1.2K} = 1.13mA$$

Open Loop KCL:

$$V_{CC} - I_C R_C - V_{CE} - I_E R_E = 0$$

Approximate Analysis $I_C \approx I_E$

$$V_{CE} = V_{CC} - I_E(R_C + R_E)$$

$$V_{CE} = 15 - 0.113 \times 10^{-2} (4.7K\Omega + 1.2K\Omega)$$

$$V_{CE} = 15 - 6.667$$

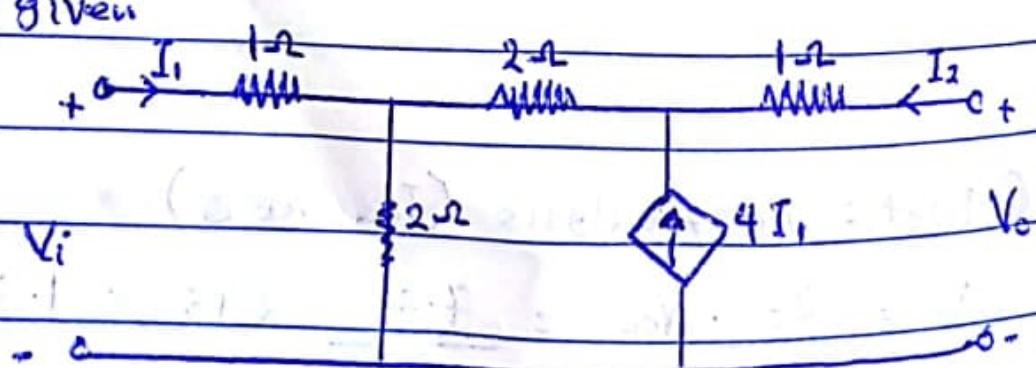
$$V_{CE} = \underline{8.33V}$$

Therefore: $V_{CE} = 8.33V$

Q-Point = $8.33V, 1.13mA$

Home-work Determine the Hybrid Parameters in the network

Given



- ① Connect IV source at Port 1 and Let Port 2 be

shortcircuted.

- (i) connect IV source at Port 2 and let Port 1 be open circuited.